

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MICRON... 3DV2C1	APPLICATION NO. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT SCHUEGRAF	
		FILING DATE Herewith	GROUP Unknown

10974 U.S. PTO
09/27/0540
01/26/01

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
<i>Sub</i>	5,043,780	08/27/91	Fazan et al.			
<i>Sub</i>	5,102,832	04/07/92	Tuttle			
<i>Sub</i>	5,110,752	05/05/92	Lu			
<i>Sub</i>	5,112,773	05/12/92	Tuttle			
<i>Sub</i>	5,130,885	07/14/92	Fazan et al.			
<i>Sub</i>	5,138,411	08/11/92	Sandhu			
<i>Sub</i>	5,182,232	01/26/93	Chhabra			
<i>Sub</i>	5,191,509	03/02/93	Wen			
<i>Sub</i>	5,318,920	06/07/94	Hayashide			
<i>Sub</i>	5,320,880	06/14/94	Sandhu et al.			
<i>Sub</i>	5,340,765	08/23/94	Dennison et al.			
<i>Sub</i>	5,366,917	11/22/94	Watanabe et al.			
<i>Sub</i>	5,366,919	11/22/94	Tanaka et al.			10/13/93
<i>Sub</i>	5,372,962	12/13/94	Hirota et al.			02/01/93
<i>Sub</i>	5,385,863	01/31/95	Tatsumi et al.			06/19/92
<i>Sub</i>	5,407,534	04/18/95	Thakur			12/10/93
<i>Sub</i>	5,413,986	1/2000	Chen et al.			
<i>Sub</i>	5,418,180	05/23/95	Brown			05/23/95
<i>Sub</i>	5,474,949	12/12/95	Hirao			01/26/93
<i>Sub</i>	5,486,488	01/23/96	Kamiyama			12/01/94
<i>Sub</i>	5,561,307	10/01/96	Mihara et al.			07/18/94
<i>Sub</i>	5,563,090	10/18/96	Lee et al.			04/10/95
<i>Sub</i>	5,569,614	10/29/96	Kataoka et al.			05/05/95
<i>Sub</i>	5,608,247	03/04/97	Brown			05/15/95
<i>Sub</i>	6,015,986	1/2000	Schuegraf			

EXAMINER

hanna Schillinger

DATE CONSIDERED

11/10/01

*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.

FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
<i>LS</i>		403136361	06/11/91	Japan	257	306		

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
<i>LS</i>	Watanabe et al., "Hemispherical Grained Si Formation on in-situ Phosphorus Doped Amorphous-Si Electrode for 256Mb DRAM's Capacitor", IEEE Transactions on Electron Devices, Vol. 42, No. 7, pp. 1247-1253, July 1995
	Watanabe et al., "An Advanced technique for Fabricating Hemispherical-Grained (HSG) Silicon Storage Electrodes", IEEE Transactions on Electron Devices, Vol. 42, No. 2, pp. 295-300, February 1995
<i>LS</i>	Sakai et al., "Novel Seeding Method for the Growth of Polycrystalline Si Films with Hemispherical Grains", Applied Physics Letters, Vol. 6, No. 2, pp. 159-161, July 13, 1992
	Kago et al., "A 0.29 μ m ² MIM CROWN Cell and Process Technologies for 1-Gigabit DRAMs", IEDM, 1194, pp. 927-929

EXAMINER	<i>hanna Schell</i>	DATE CONSIDERED	<i>11/10/07</i>
<p>*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.</p>			